# **Amplifier Transistors**

## **NPN Silicon**

## Features

• Pb-Free Packages are Available\*

## **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
Collector – Emitter Voltage 2N5088 2N5089		30 25	Vdc
Collector – Base Voltage 2N5088 2N5089		35 30	Vdc
Emitter – Base Voltage	$V_{\text{EBO}}$	3.0	Vdc
Collector Current – Continuous	۱ <sub>C</sub>	50	mAdc
Total Device Dissipation @ $T_A = 25^{\circ}C$ Derate above 25°C	P <sub>D</sub>	625 5.0	mW mW/°C
Total Device Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-Case	$R_{\thetaJC}$	83.3	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. R<sub>0JA</sub> is measured with the device soldered into a typical printed circuit board.



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## 2N 508x AYWW

x = 8 or 9 A = Assembly Location Y = Year WW = Work Week = Pb–Free Package (Note: Microdot may be in either location)

## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
2N5088G	TO-92 (Pb-Free)	5000 Units/Bulk
2N2088RLRAG	TO–92 (Pb–Free)	2000/Tape & Reel
2N5089G	TO–92 (Pb–Free)	5000 Units/Bulk
2N2089RLRE	TO-92	2000/Tape & Reel

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

## **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (Note 2) $(I_C = 1.0 \text{ mAdc}, I_B = 0)$	2N5088 2N5089	V <sub>(BR)CEO</sub>	30 25		Vdc
Collector – Base Breakdown Voltage ( $I_C = 100 \ \mu Adc, I_E = 0$ )	2N5088 2N5089	V <sub>(BR)CBO</sub>	35 30		Vdc
Collector Cutoff Current $(V_{CB} = 20 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 15 \text{ Vdc}, I_E = 0)$	2N5088 2N5089	I <sub>CBO</sub>		50 50	nAdc
		I <sub>EBO</sub>	-	50 100	nAdc
ON CHARACTERISTICS				-	
DC Current Gain ( $I_C = 100 \ \mu Adc, \ V_{CE} = 5.0 \ Vdc$ )	2N5088 2N5089	h <sub>FE</sub>	300 400	900 1200	_
(I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 5.0 Vdc)	2N5088 2N5089	-	350 450	-	
$(I_C = 10 \text{ mAdc}, V_{CE} = 5.0 \text{ Vdc})$ (Note 2)	<b>2N</b> 5088 2N5089	1312 CN	300 400	_ _	
Collector – Emitter Saturation Voltage (I <sub>C</sub> = 10 mAdc, I <sub>B</sub> = 1.0 mAdc)	32	V <sub>CE(sat)</sub>	_	0.5	Vdc
Base – Emitter On Voltage (I <sub>C</sub> = 10 mAdc, V <sub>CE</sub> = 5.0 Vdc) (Note 2)		V <sub>BE(on)</sub>	_	0.8	Vdc
SMALL-SIGNAL CHARACTERISTICS					
Current–Gain – Bandwidth Product (I <sub>C</sub> = 500 μAdc, V <sub>CE</sub> = 5.0 Vdc, f = 20 MHz)		f <sub>T</sub>	50	-	MHz
Collector–Base Capacitance (V <sub>CB</sub> = 5.0 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)		C <sub>cb</sub>	-	4.0	pF
Emitter–Base Capacitance ( $V_{EB} = 0.5 \text{ Vdc}, I_C = 0, f = 1.0 \text{ MHz}$ )		C <sub>eb</sub>	-	10	pF
Small–Signal Current Gain (I <sub>C</sub> = 1.0 mAdc, V <sub>CE</sub> = 5.0 Vdc, f = 1.0 kHz)	2N5088 2N5089	h <sub>fe</sub>	350 450	1400 1800	-
Noise Figure (I <sub>C</sub> = 100 $\mu$ Adc, V <sub>CE</sub> = 5.0 Vdc, R <sub>S</sub> = 1.0 kΩ, f = 1.0 kHz)	2N5088 2N5089	NF		3.0 2.0	dB

2. Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2.0%.

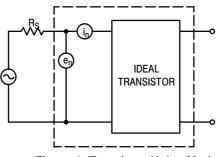
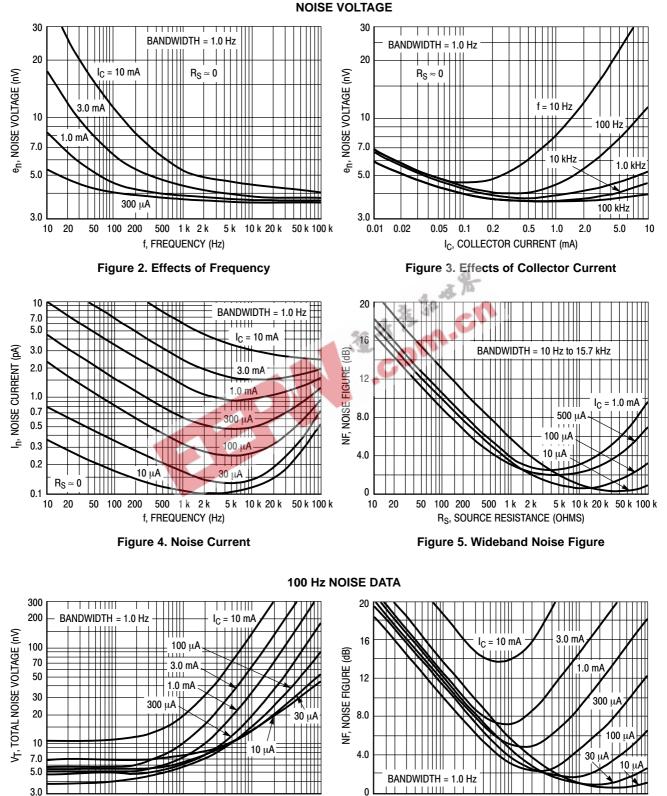


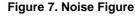
Figure 1. Transistor Noise Model

## **NOISE CHARACTERISTICS**

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}C)$ 



NOISE VOLTAGE



500 1 k 2 k

R<sub>S</sub>, SOURCE RESISTANCE (OHMS)

5 k 10 k 20 k 50 k 100 k

10 20 50 100 200

5 k 10 k 20 k 50 k 100 k

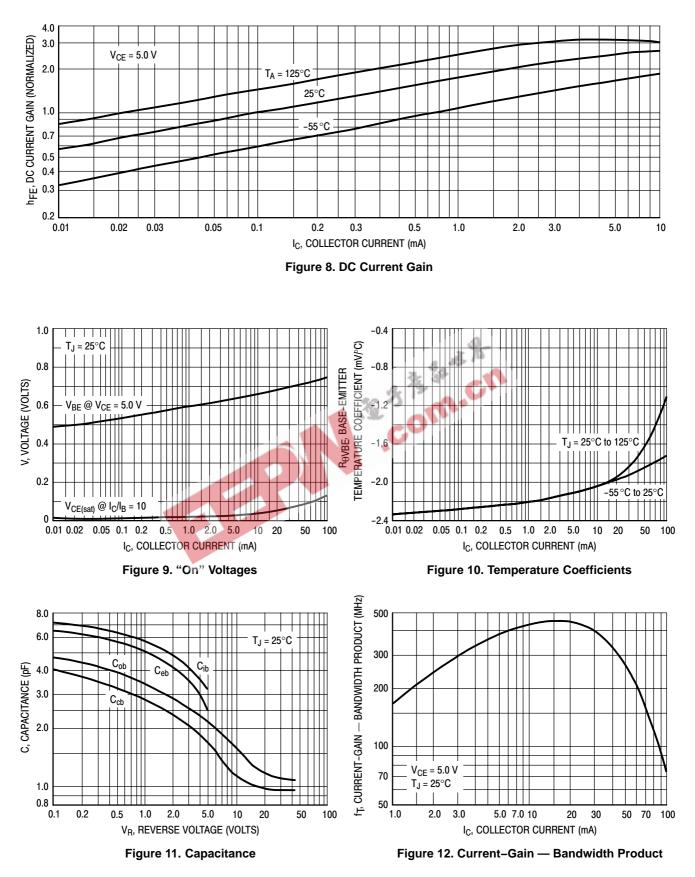
10 20

50 100 200

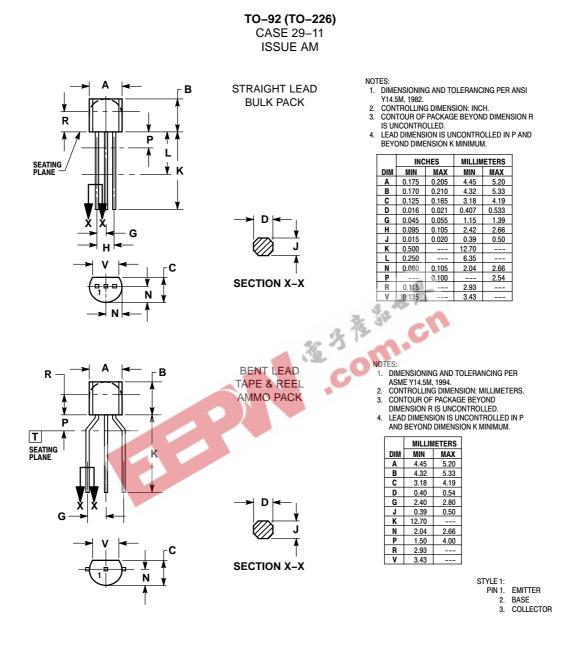
500 1 k 2 k

R<sub>S</sub>, SOURCE RESISTANCE (OHMS)

Figure 6. Total Noise Voltage



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